

Åæmit Å-zgÅ^{1/4}r

List of Publications by Year in descending order

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48
papers

2,620
citations

430874

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265206

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all docs

48
docs citations

48
times ranked

3599
citing authors

#	ARTICLE	IF	CITATIONS
1	Energy-Efficient, On-Demand Activation of Biosensor Arrays for Long-Term Continuous Health Monitoring. <i>Biosensors</i> , 2022, 12, 358.	4.7	2
2	A Platform for Complementary Metal-Oxide-Semiconductor Compatible Plasmonics: High Plasmonic Quality Titanium Nitride Thin Films on Si (001) with a MgO Interlayer. <i>Advanced Photonics Research</i> , 2021, 2, 2000210.	3.6	8
3	High-Quality Plasmonic Materials TiN and ZnO:Al by Atomic Layer Deposition. <i>Physica Status Solidi - Rapid Research Letters</i> , 2021, 15, 2100227.	2.4	4
4	Solution-Processed Ge _{1-x} Sn _x Alloy Nanocrystal Thin Films with High Electrical Conductivity and Tunable Energy Gaps. <i>Chemistry of Materials</i> , 2021, 33, 6897-6908.	6.7	5
5	High-Performance BeMgZnO/ZnO Heterostructure Field-Effect Transistors. <i>Physica Status Solidi - Rapid Research Letters</i> , 2020, 14, 2000371.	2.4	10
6	Plasmonic titanium nitride via atomic layer deposition: A low-temperature route. <i>Journal of Applied Physics</i> , 2020, 127, .	2.5	12
7	Comparative study of BeMgZnO/ZnO heterostructures on c-sapphire and GaN by molecular beam epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020, 38, .	2.1	3
8	Design and Optimization of an Acoustic Metamaterial Lens. , 2020, , .		0
9	Micro-LEDs, a Manufacturability Perspective. <i>Applied Sciences (Switzerland)</i> , 2019, 9, 1206.	2.5	188
10	Facile synthesis of highly luminescent lithium silicate nanocrystals with varying crystal structures and morphology. <i>CrystEngComm</i> , 2019, 21, 1974-1983.	2.6	11
11	Characterization of Ag Schottky Barriers on Be _{0.02} Mg _{0.26} ZnO/ZnO Heterostructures. <i>Physica Status Solidi - Rapid Research Letters</i> , 2018, 12, 1700366.	2.4	9
12	Polarity Control within One Monolayer at ZnO/GaN Heterointerface: (0001) Plane Inversion Domain Boundary. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 37651-37660.	8.0	5
13	Fabrication of Schottky Diodes on Zn-polar BeMgZnO/ZnO Heterostructure Grown by Plasma-assisted Molecular Beam Epitaxy. <i>Journal of Visualized Experiments</i> , 2018, , .	0.3	1
14	Influence of ZnO thin film crystallinity on <i>in vitro</i> biocompatibility. <i>Toxicology Research</i> , 2018, 7, 754-759.	2.1	6
15	Recent Development of Boron Nitride towards Electronic Applications. <i>Advanced Electronic Materials</i> , 2017, 3, 1600485.	5.1	98
16	Hot-electron noise spectroscopy for HFET channels. , 2017, , .		2
17	Status of Growth of Group III-Nitride Heterostructures for Deep Ultraviolet Light-Emitting Diodes. <i>Crystals</i> , 2017, 7, 300.	2.2	39
18	Ultra-small Ge _{1-x} Sn _x quantum dots with visible photoluminescence. <i>Chemical Communications</i> , 2016, 52, 11665-11668.	4.1	30

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19	Energy Gap Tuning and Carrier Dynamics in Colloidal Ge _x Sn _{1-x} Quantum Dots. <i>Journal of Physical Chemistry Letters</i> , 2016, 7, 3295-3301.	4.6	23
20	Polarity control and residual strain in ZnO epilayers grown by molecular beam epitaxy on (0001) GaN/sapphire. <i>Physica Status Solidi - Rapid Research Letters</i> , 2016, 10, 682-686.	2.4	19
21	Metal-Semiconductor Hybrid Aerogels: Evolution of Optoelectronic Properties in a Low-Dimensional CdSe/Ag Nanoparticle Assembly. <i>ACS Nano</i> , 2015, 9, 9810-9821.	14.6	44
22	Thickness Variations and Absence of Lateral Compositional Fluctuations in Aberration-Corrected STEM Images of InGaN LED Active Regions at Low Dose. <i>Microscopy and Microanalysis</i> , 2014, 20, 864-868.	0.4	10
23	Electron energy relaxation in wurtzite ZnO and GaN. , 2013, , .		1
24	Enhanced microwave dielectric tunability of Ba _{0.5} Sr _{0.5} TiO ₃ thin films grown with reduced strain on DyScO ₃ substrates by three-step technique. <i>Journal of Applied Physics</i> , 2013, 113, 044108.	2.5	13
25	Carrier dynamics in bulk GaN. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	65
26	Carrier dynamics under two- and single-photon excitation in bulk GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2012, 249, 503-506.	1.5	4
27	The effect of barrier strain on the reliability of In _x Al _{1-x} N/AlN/GaN heterostructure field-effect transistors. <i>Physica Status Solidi - Rapid Research Letters</i> , 2012, 6, 163-165.	2.4	1
28	Measurements of generation-recombination effect by low-frequency phase-noise technique in AlGaIn/GaN MOSHFETs. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 1539-1543.	0.8	6
29	Reduction of Flicker Noise in AlGaIn/GaN-Based HFETs After High Electric-Field Stress. <i>IEEE Electron Device Letters</i> , 2011, 32, 1513-1515.	3.9	4
30	Field-assisted emission in AlGaIn/GaN heterostructure field-effect transistors using low-frequency noise technique. <i>Journal of Applied Physics</i> , 2011, 109, .	2.5	19
31	ZnO Devices and Applications: A Review of Current Status and Future Prospects. <i>Proceedings of the IEEE</i> , 2010, 98, 1255-1268.	21.3	669
32	GaN-Based Light-Emitting Diodes: Efficiency at High Injection Levels. <i>Proceedings of the IEEE</i> , 2010, 98, 1180-1196.	21.3	103
33	Ferromagnetism in ZnO- and GaN-Based Diluted Magnetic Semiconductors: Achievements and Challenges. <i>Proceedings of the IEEE</i> , 2010, 98, 1288-1301.	21.3	26
34	Stress test measurements of lattice-matched InAlN/AlN/GaN HFET structures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010, 207, 1345-1347.	1.8	2
35	Effect of large strain on dielectric and ferroelectric properties of Ba _{0.5} Sr _{0.5} TiO ₃ thin films. <i>Applied Physics Letters</i> , 2009, 95, 012907.	3.3	15
36	Epitaxial growth of (001)-oriented Ba _{0.5} Sr _{0.5} TiO ₃ thin films on a-plane sapphire with an MgO/ZnO bridge layer. <i>Applied Physics Letters</i> , 2009, 95, 212901.	3.3	17

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37	Microwave ferrites, part 1: fundamental properties. Journal of Materials Science: Materials in Electronics, 2009, 20, 789-834.	2.2	348
38	Microwave ferrites, part 2: passive components and electrical tuning. Journal of Materials Science: Materials in Electronics, 2009, 20, 911-952.	2.2	110
39	Large pyroelectric effect in undoped epitaxial Pb(Zr,Ti)O ₃ thin films on SrTiO ₃ substrates. Applied Physics Letters, 2008, 93, 052913.	3.3	27
40	On the efficiency droop in InGaN multiple quantum well blue light emitting diodes and its reduction with p-doped quantum well barriers. Applied Physics Letters, 2008, 93, .	3.3	301
41	Reduction of efficiency droop in InGaN light emitting diodes by coupled quantum wells. Applied Physics Letters, 2008, 93, .	3.3	208
42	Large electro-optic effect in single-crystal Pb(Zr,Ti)O ₃ (001) measured by spectroscopic ellipsometry. Journal of Applied Physics, 2008, 104, 093103.	2.5	18
43	Photoelectrochemical Etching of GaN Thin Films With Varying Carrier Concentrations. Materials Research Society Symposia Proceedings, 2007, 1040, 1.	0.1	0
44	High electron mobility in nearly lattice-matched AlInN/AlN/GaN heterostructure field effect transistors. Applied Physics Letters, 2007, 91, 132116.	3.3	107
45	Defect reduction in GaN epilayers grown by metal-organic chemical vapor deposition with in situ SiNx nanonetwork. Applied Physics Letters, 2007, 90, 262112.	3.3	21
46	Persistent Photoconductivity in High-mobility Al _x Ga _{1-x} N/AlN/GaN Heterostructures Grown by Metal-organic Vapor-phase Epitaxy. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
47	Structural and Optical Properties of PbTiO ₃ Grown on SrTiO ₃ Substrates by Peroxide MBE. Materials Research Society Symposia Proceedings, 2006, 966, 1.	0.1	4
48	Growth of High-Quality Pb(Zr _x Ti _{1-x})O ₃ Films by Peroxide MBE and Their Optical and Structural Characteristics. Materials Research Society Symposia Proceedings, 2006, 966, 1.	0.1	2